

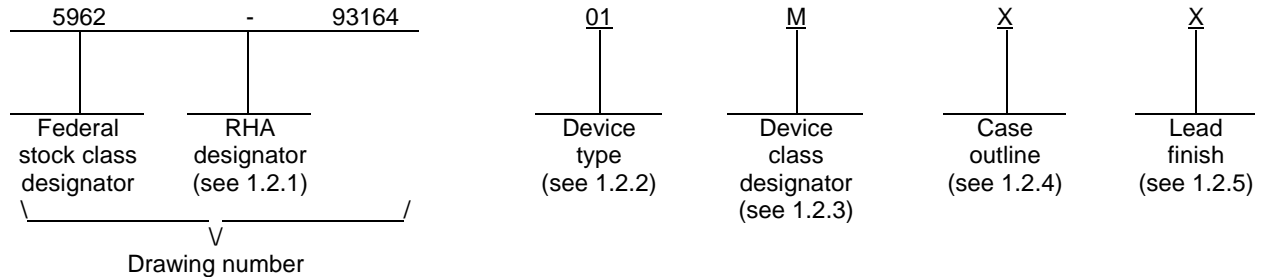
REVISIONS			
LTR	DESCRIPTION	DATE (YR-MO-DA)	APPROVED
A	Drawing updated to reflect current requirements. - ro	02-03-07	R. MONNIN

REV																				
SHEET																				
REV	A	A	A	A	A															
SHEET	15	16	17	18	19															
REV STATUS OF SHEETS	REV			A	A	A	A	A	A	A	A	A	A	A	A	A	A	A	A	
	SHEET			1	2	3	4	5	6	7	8	9	10	11	12	13	14			
PMIC N/A	PREPARED BY SANDRA ROONEY				<b>DEFENSE SUPPLY CENTER COLUMBUS</b> <b>COLUMBUS, OHIO 43216</b> <a href="http://www.dsccl.dla.mil">http://www.dsccl.dla.mil</a>															
<b>STANDARD MICROCIRCUIT DRAWING</b>  THIS DRAWING IS AVAILABLE FOR USE BY ALL DEPARTMENTS AND AGENCIES OF THE DEPARTMENT OF DEFENSE  AMSC N/A	CHECKED BY CHARLES E. BESORE																			
	APPROVED BY MICHAEL A. FRYE																			
	DRAWING APPROVAL DATE 93-11-05																			
	REVISION LEVEL A																			
				SIZE A	CAGE CODE <b>67268</b>	<b>5962-93164</b>														
				SHEET		1 OF 19														

1. SCOPE

1.1 Scope. This drawing documents two product assurance class levels consisting of high reliability (device classes Q and M) and space application (device class V). A choice of case outlines and lead finishes are available and are reflected in the Part or Identifying Number (PIN). When available, a choice of Radiation Hardness Assurance (RHA) levels are reflected in the PIN.

1.2 PIN. The PIN is as shown in the following example:



1.3 Absolute maximum ratings. (unless otherwise specified,  $T_A = +25^\circ\text{C}$ )

$V_{CC}$ to digital common .....	+16.5 V
$V_{EE}$ to digital common .....	-16.5 V
$V_{LOGIC}$ to digital common .....	+7 V
Analog common to digital common .....	$\pm 1.0$ V
Control inputs ( $\overline{CE}$ , $\overline{CS}$ , $A_0$ , $12/\overline{8}$ , $R/\overline{C}$ ) to digital common .....	-0.5 V to $V_{LOGIC} + 0.5$ V
Analog inputs (REF IN, BIP OFF, $10 V_{IN}$ ) to analog common .....	$V_{EE}$ to $V_{CC}$
$20 V_{IN}$ to analog common .....	$V_{EE}$ to +24 V
REF OUT .....	Indefinite short to common Momentary short to $V_{CC}$
Power dissipation ( $P_D$ ) .....	825 mW
Storage temperature range .....	$-65^\circ\text{C}$ to $+150^\circ\text{C}$
Lead temperature (soldering 10 seconds) .....	$+300^\circ\text{C}$
Junction temperature ( $T_J$ ) .....	$+175^\circ\text{C}$
Thermal resistance, junction-to-case ( $\theta_{JC}$ ) .....	See MIL-STD-1835
Thermal resistance, junction-to-ambient ( $\theta_{JA}$ ) .....	$60^\circ\text{C/W}$

1.4 Recommended operating conditions.

Ambient operating temperature range ( $T_A$ ) .....	$-55^\circ\text{C}$ to $125^\circ\text{C}$
Operating voltage range:	
$V_{CC}$ to digital common .....	+11.4 V dc to +16.5 V dc
$V_{EE}$ to digital common .....	-11.4 V dc to -16.5 V dc
$V_{LOGIC}$ to digital common .....	+4.5 V dc to +5.5 V dc

2. APPLICABLE DOCUMENTS

2.1 Government specification, standards, and handbooks. The following specification, standards, and handbooks form a part of this drawing to the extent specified herein. Unless otherwise specified, the issues of these documents are those listed in the issue of the Department of Defense Index of Specifications and Standards (DoDISS) and supplement thereto, cited in the solicitation.

SPECIFICATION

DEPARTMENT OF DEFENSE

MIL-PRF-38535 - Integrated Circuits, Manufacturing, General Specification for.

STANDARDS

DEPARTMENT OF DEFENSE

MIL-STD-883 - Test Method Standard Microcircuits.  
MIL-STD-1835 - Interface Standard Electronic Component Case Outlines.

<b>STANDARD MICROCIRCUIT DRAWING</b> DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 43216-5000	SIZE <b>A</b>		<b>5962-93164</b>
		REVISION LEVEL <b>A</b>	SHEET <b>3</b>

HANDBOOKS

DEPARTMENT OF DEFENSE

- MIL-HDBK-103 - List of Standard Microcircuit Drawings.
- MIL-HDBK-780 - Standard Microcircuit Drawings.

(Unless otherwise indicated, copies of the specification, standards, and handbooks are available from the Standardization Document Order Desk, 700 Robbins Avenue, Building 4D, Philadelphia, PA 19111-5094.)

2.2 Order of precedence. In the event of a conflict between the text of this drawing and the references cited herein, the text of this drawing takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

3. REQUIREMENTS

3.1 Item requirements. The individual item requirements for device classes Q and V shall be in accordance with MIL-PRF-38535 and as specified herein or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein. The individual item requirements for device class M shall be in accordance with MIL-PRF-38535, appendix A for non-JAN class level B devices and as specified herein.

3.2 Design, construction, and physical dimensions. The design, construction, and physical dimensions shall be as specified in MIL-PRF-38535 and herein for device classes Q and V or MIL-PRF-38535, appendix A and herein for device class M.

3.2.1 Case outline. The case outline shall be in accordance with 1.2.4 herein.

3.2.2 Terminal connections. The terminal connections shall be as specified on figure 1.

3.2.3 Truth table. The truth table shall be as specified on figure 2.

3.2.4 Functional block diagram. The functional block diagram shall be as specified on figure 3.

3.3 Electrical performance characteristics and post irradiation parameter limits. Unless otherwise specified herein, the electrical performance characteristics and post irradiation parameter limits are as specified in table I and shall apply over the full ambient operating temperature range.

3.4 Electrical test requirements. The electrical test requirements shall be the subgroups specified in table II. The electrical tests for each subgroup are defined in table I.

3.5 Marking. The part shall be marked with the PIN listed in 1.2 herein. In addition, the manufacturer's PIN may also be marked as listed in MIL-HDBK-103. For packages where marking of the entire SMD PIN number is not feasible due to space limitations, the manufacturer has the option of not marking the "5962-" on the device. For RHA product using this option, the RHA designator shall still be marked. Marking for device classes Q and V shall be in accordance with MIL-PRF-38535. Marking for device class M shall be in accordance with MIL-PRF-38535, appendix A.

3.5.1 Certification/compliance mark. The certification mark for device classes Q and V shall be a "QML" or "Q" as required in MIL-PRF-38535. The compliance mark for device class M shall be a "C" as required in MIL-PRF-38535, appendix A.

3.6 Certificate of compliance. For device classes Q and V, a certificate of compliance shall be required from a QML-38535 listed manufacturer in order to supply to the requirements of this drawing (see 6.6.1 herein). For device class M, a certificate of compliance shall be required from a manufacturer in order to be listed as an approved source of supply in MIL-HDBK-103 (see 6.6.2 herein). The certificate of compliance submitted to DSCC-VA prior to listing as an approved source of supply for this drawing shall affirm that the manufacturer's product meets, for device classes Q and V, the requirements of MIL-PRF-38535 and herein or for device class M, the requirements of MIL-PRF-38535, appendix A and herein.

<b>STANDARD MICROCIRCUIT DRAWING</b> DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 43216-5000	SIZE <b>A</b>		<b>5962-93164</b>
		REVISION LEVEL <b>A</b>	SHEET <b>4</b>

TABLE I. Electrical performance characteristics.

Test	Symbol	Conditions <sup>1/</sup> -55°C ≤ T <sub>A</sub> ≤ +125°C V <sub>CC</sub> = +15 V, V <sub>EE</sub> = -15 V,  V <sub>LOGIC</sub> = +5 V unless otherwise specified	Group A subgroups	Device type	Limits		Unit
					Min	Max	
Power dissipation	P <sub>D</sub>	Three-stated outputs	1,2,3	01		575	mW
Input resistance	R <sub>IN</sub>	10 V span, T <sub>A</sub> = +25°C	1	01	3	7	kΩ
		20 V span, T <sub>A</sub> = +25°C			6	14	
Internal reference <sup>2/</sup> output voltage	V <sub>REF</sub>	Bipolar 20 V span, 2.0 mA external load, T <sub>A</sub> = +25°C	1	01	9.9	10.1	V
Logic input high voltage (CE, $\overline{CS}$ , R/ $\overline{C}$ , A <sub>O</sub> )	V <sub>IH</sub>		1,2,3	01	2.0		V
Logic input low voltage (CE, $\overline{CS}$ , R/ $\overline{C}$ , A <sub>O</sub> )	V <sub>IL</sub>		1,2,3	01		0.8	V
Logic input current (CE, $\overline{CS}$ , R/ $\overline{C}$ , A <sub>O</sub> )	I <sub>LIN</sub>	V <sub>IH</sub> = 5.0 V, V <sub>IL</sub> = 0.0 V	1,2,3	01	-10	+10	μA
Logic output high voltage (DB11-DB0)	V <sub>OH</sub>	I <sub>SOURCE</sub> = 500 μA	1,2,3	01	2.4		V
Logic output low voltage (DB11-DB0, STS)	V <sub>OL</sub>	I <sub>SINK</sub> = 1.6 mA	1,2,3	01		0.4	V
Three-state output leakage (DB11-DB0)	I <sub>OLT</sub>	Outputs three-stated, V <sub>IH</sub> = 5.0 V	1,2,3	01	-10	+10	μA
Power supply current	I <sub>LOGIC</sub>	Outputs three-stated, REF OUT to REF IN through 50 Ω, V <sub>CC</sub> = 16.5 V, V <sub>EE</sub> = -16.5 V, V <sub>LOGIC</sub> = 5.5 V	1,2,3	01		8	mA
	I <sub>CC</sub>					14	
	I <sub>EE</sub>					18	
Integral nonlinearity	INL	Major transitions, unipolar 10 V span, bipolar 20 V span	1	01	-0.5	+0.5	LSB
			2,3		-1.0	+1.0	
Differential nonlinearity <sup>3/</sup>	DNL	All codes tested, unipolar 10 V span, bipolar 20 V span	1,2,3	01	12		Bits

See footnotes at end of table.

**STANDARD  
MICROCIRCUIT DRAWING**  
DEFENSE SUPPLY CENTER COLUMBUS  
COLUMBUS, OHIO 43216-5000

SIZE  
**A**

REVISION LEVEL  
**A**

**5962-93164**

SHEET  
**5**

TABLE I. Electrical performance characteristics – Continued.

Test	Symbol	Conditions <sup>1/</sup> -55°C ≤ T <sub>A</sub> ≤ +125°C V <sub>CC</sub> = +15 V, V <sub>EE</sub> = -15 V, V <sub>LOGIC</sub> = +5 V unless otherwise specified	Group A subgroups	Device type	Limits		Unit
					Min	Max	
Power supply rejection <sup>4/</sup>	PSR	Unipolar-10 V span <sup>5/</sup>	1,2,3	01	-1	+1	LSB
		<sup>6/</sup>			-0.5	+0.5	
		<sup>7/</sup>			-1	+1	
Unipolar offset error	V <sub>OSE</sub>	10 V span, T <sub>A</sub> = +25°C	1	01	-2	+2	LSB
Unipolar offset drift	TC <sub>VOS</sub>	10 V span	2,3	01	-1	+1	LSB
Bipolar offset error	B <sub>POE</sub>	20 V span, T <sub>A</sub> = +25°C	1	01	-3	+3	LSB
Bipolar offset drift	TCB <sub>POE</sub>	20 V span	2,3	01	-2	+2	LSB
Full-scale calibration error	A <sub>B</sub>	Bipolar 20 V span, T <sub>A</sub> = +25°C	1	01	-0.125	+0.125	% of FSR
	A <sub>U</sub>	Unipolar 10 V span, T <sub>A</sub> = +25°C			-0.125	+0.125	
Full-scale calibration drift	TCA <sub>E</sub>	Bipolar 20 V span	2,3	01	-7	+7	LSB
Signal to noise and distortion	S/(N+D)	f <sub>IN</sub> = 10 kHz, f <sub>SAMPLE</sub> = 100 kSPS	4,5,6	01	70		dB
Total harmonic distortion	THD	f <sub>IN</sub> = 10 kHz, f <sub>SAMPLE</sub> = 100 kSPS	4,5,6	01		-82	dB
Peak spurious or harmonic component		f <sub>IN</sub> = 10 kHz, f <sub>SAMPLE</sub> = 100 kSPS	4,5,6	01		-82	dB
Intermodulation <sup>8/</sup> distortion	IMD	Second order products	4,5,6	01		-80	dB
		Third order products				-80	
Functional tests		See 4.4.1b	7,8				

See footnotes at end of table.

**STANDARD  
MICROCIRCUIT DRAWING**  
DEFENSE SUPPLY CENTER COLUMBUS  
COLUMBUS, OHIO 43216-5000

SIZE  
**A**

REVISION LEVEL  
**A**

**5962-93164**

SHEET  
**6**

TABLE I. Electrical performance characteristics – Continued.

Test	Symbol	Conditions 1/ -55°C ≤ T <sub>A</sub> ≤ +125°C V <sub>CC</sub> = +15 V, V <sub>EE</sub> = -15 V,  V <sub>LOGIC</sub> = +5 V unless otherwise specified	Group A subgroups	Device type	Limits		Unit
					Min	Max	

Converter start timing section (see figure 4)

Conversion time	t <sub>C</sub>	8-bit cycle	9,10,11	01		8	μs
		12-bits cycle				10	
STS delay from CE	t <sub>DSC</sub>		9	01		200	ns
			10,11			225	
CE pulse width	t <sub>HEC</sub>		9,10,11	01	50		ns
$\overline{CS}$ to CE setup	t <sub>SSC</sub>		9,10,11	01	50		ns
$\overline{CS}$ low during CE high	t <sub>HSC</sub>		9,10,11	01	50		ns
R/ $\overline{C}$ to CE setup	t <sub>SRC</sub>		9,10,11	01	50		ns
R/ $\overline{C}$ low during CE high	t <sub>HRC</sub>		9,10,11	01	50		ns
A <sub>O</sub> to CE setup	t <sub>SAC</sub>		9,10,11	01	0		ns
A <sub>O</sub> valid during CE high	t <sub>HAC</sub>		9,10,11	01	50		ns

Read timing full control mode section (see figure 5)

Access time	t <sub>DD</sub>	See figures 8 and 9	9,10,11	01		150	ns
Data valid after CE low	t <sub>HD</sub>	See figures 8 and 9	9	01	25		ns
			10,11		15		
Output float delay	t <sub>HL</sub>	See figures 8 and 9	9,10,11	01		150	ns

See footnotes at end of table.

**STANDARD  
MICROCIRCUIT DRAWING**  
DEFENSE SUPPLY CENTER COLUMBUS  
COLUMBUS, OHIO 43216-5000

SIZE  
**A**

REVISION LEVEL  
**A**

**5962-93164**

SHEET  
**7**

TABLE I. Electrical performance characteristics – Continued.

Test	Symbol	Conditions 1/ -55°C ≤ T <sub>A</sub> ≤ +125°C V <sub>CC</sub> = +15 V, V <sub>EE</sub> = -15 V,  V <sub>LOGIC</sub> = +5 V unless otherwise specified	Group A subgroups	Device type	Limits		Unit
					Min	Max	

Read timing full control mode section - continued (see figure 5)

$\overline{\text{CS}}$ to CE setup	t <sub>SSR</sub>		9,10,11	01	50		ns
R/ $\overline{\text{C}}$ to CE setup	t <sub>SRR</sub>		9,10,11	01	0		ns
A <sub>O</sub> to CE setup	t <sub>SAR</sub>		9,10,11	01	50		ns
$\overline{\text{CS}}$ valid after CE low	t <sub>HSR</sub>		9,10,11	01	0		ns
R/ $\overline{\text{C}}$ high after CE low	t <sub>HRR</sub>		9,10,11	01	0		ns
A <sub>O</sub> valid after CE low	t <sub>HAR</sub>		9,10,11	01	50		ns

Read timing stand alone mode (see figures 6 and 7)

Data access time	t <sub>DDR</sub>	See figures 8 and 9	9,10,11	01		150	ns
Low R/ $\overline{\text{C}}$ pulse width	t <sub>HRL</sub>		9,10,11	01	50		ns
STS delay from R/ $\overline{\text{C}}$	t <sub>DS</sub>		9	01		200	ns
			10,11			225	
Data valid after R/ $\overline{\text{C}}$ low	t <sub>HDR</sub>	See figures 8 and 9	9,10,11	01	25		ns
STS delay after data valid	t <sub>HS</sub>		9,10,11	01	0.6	1.2	μs
High R/ $\overline{\text{C}}$ pulse width	t <sub>HRH</sub>		9,10,11	01	150		ns

See footnotes at end of table.

**STANDARD  
MICROCIRCUIT DRAWING**  
DEFENSE SUPPLY CENTER COLUMBUS  
COLUMBUS, OHIO 43216-5000

SIZE  
**A**

REVISION LEVEL  
**A**

**5962-93164**

SHEET  
**8**



TABLE I. Electrical performance characteristics – Continued.

- 1/ Unless otherwise specified,  $T_{MIN}$  to  $T_{MAX}$ ,  $V_{CC} = +15\text{ V} \pm 10\%$  or  $+12\text{ V} \pm 5\%$ ,  $V_{LOGIC} = +5\text{ V} \pm 10\%$ ,  $V_{EE} = -15\text{ V} \pm 10\%$  or  $-12\text{ V} \pm 5\%$ ; 12/8 connected to  $V_{LOGIC}$ ,  $A_0$  and  $\overline{CS}$  at logic "0", CE at logic "1." 10 V unipolar-50  $\Omega$  resistor REF OUT to REF IN, 50  $\Omega$  resistor BIP OFF to ground. Analog input connected to 10  $V_{IN}$ . 20 V bipolar-50  $\Omega$  resistor REF OUT to BIP OFF, 50  $\Omega$  resistor REF OUT to REF IN. Analog input connected to 20  $V_{IN}$ .
- 2/ The reference should be buffered for operation on  $\pm 12\text{ V}$  supplies.
- 3/ Minimum resolution for which no missing codes are guaranteed.
- 4/ Change in the full-scale unipolar 10 V span as power supply voltage is varied from min to max specified value.
- 5/ Test conditions for PSRR:  $13.5\text{ V} \leq V_{CC} \leq 16.5\text{ V}$ ,  $V_{LOGIC} = 5\text{ V}$ ,  $V_{EE} = -15\text{ V}$ ;  $11.4\text{ V} \leq V_{CC} \leq 12.6\text{ V}$ ,  $V_{LOGIC} = 5\text{ V}$ ,  $V_{EE} = -12\text{ V}$ .
- 6/  $4.5\text{ V} \leq V_{LOGIC} \leq 5.5\text{ V}$ ,  $V_{CC} = 15\text{ V}$ ,  $V_{EE} = -15\text{ V}$ .
- 7/  $-16.5\text{ V} \leq V_{EE} \leq -13.5\text{ V}$ ,  $V_{LOGIC} = 5\text{ V}$ ,  $V_{CC} = 15\text{ V}$ ;  $-12.6\text{ V} \leq V_{EE} \leq -11.4\text{ V}$ ,  $V_{LOGIC} = 5\text{ V}$ ,  $V_{CC} = 12\text{ V}$ .
- 8/  $f_a = 9.08\text{ kHz}$ ,  $f_b = 9.58\text{ kHz}$  with  $f_{SAMPLE} = 100\text{ kHz}$ .

3.7 Certificate of conformance. A certificate of conformance as required for device classes Q and V in MIL-PRF-38535 or for device class M in MIL-PRF-38535, appendix A shall be provided with each lot of microcircuits delivered to this drawing.

3.8 Notification of change for device class M. For device class M, notification to DSCC-VA of change of product (see 6.2 herein) involving devices acquired to this drawing is required for any change as defined in MIL-PRF-38535, appendix A.

3.9 Verification and review for device class M. For device class M, DSCC, DSCC's agent, and the acquiring activity retain the option to review the manufacturer's facility and applicable required documentation. Offshore documentation shall be made available onshore at the option of the reviewer.

3.10 Microcircuit group assignment for device class M. Device class M devices covered by this drawing shall be in microcircuit group number 93 (see MIL-PRF-38535, appendix A).

<b>STANDARD MICROCIRCUIT DRAWING</b> DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 43216-5000	SIZE <b>A</b>		<b>5962-93164</b>
		REVISION LEVEL <b>A</b>	SHEET <b>9</b>

Device type	01
Case outline	X
Terminal number	Terminal symbol
1	V <sub>LOGIC</sub>
2	12/ $\bar{8}$
3	$\bar{CS}$
4	A <sub>O</sub>
5	R/ $\bar{C}$
6	CE
7	V <sub>CC</sub>
8	REF <sub>OUT</sub>
9	AC
10	REF <sub>IN</sub>
11	V <sub>EE</sub>
12	BIP OFF
13	10 V <sub>IN</sub>
14	20 V <sub>IN</sub>
15	DC
16	DB0
17	DB1
18	DB2
19	DB3
20	DB4
21	DB5
22	DB6
23	DB7
24	DB8
25	DB9
26	DB10
27	DB11
28	STS

FIGURE 1. Terminal connections.

<b>STANDARD MICROCIRCUIT DRAWING</b> DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 43216-5000	SIZE <b>A</b>		<b>5962-93164</b>
		REVISION LEVEL <b>A</b>	SHEET <b>10</b>

CE	$\overline{CS}$	$R/\overline{C}$	$12/\overline{8}$	AO	Operation
0	X	X	X	X	None
X	1	X	X	X	None
1	0	0	X	0	Initiate 12 bit conversion
1	0	0	X	1	Initiate 8 bit conversion
1	0	1	1	X	Enable 12 bit parallel output
1	0	1	0	0	Enable 8 most significant bits
1	0	1	0	1	Enable 4 LSBs and 4 trailing zeros

FIGURE 2. Truth table.

**STANDARD  
MICROCIRCUIT DRAWING**  
DEFENSE SUPPLY CENTER COLUMBUS  
COLUMBUS, OHIO 43216-5000

SIZE  
**A**

REVISION LEVEL  
**A**

**5962-93164**

SHEET  
**11**



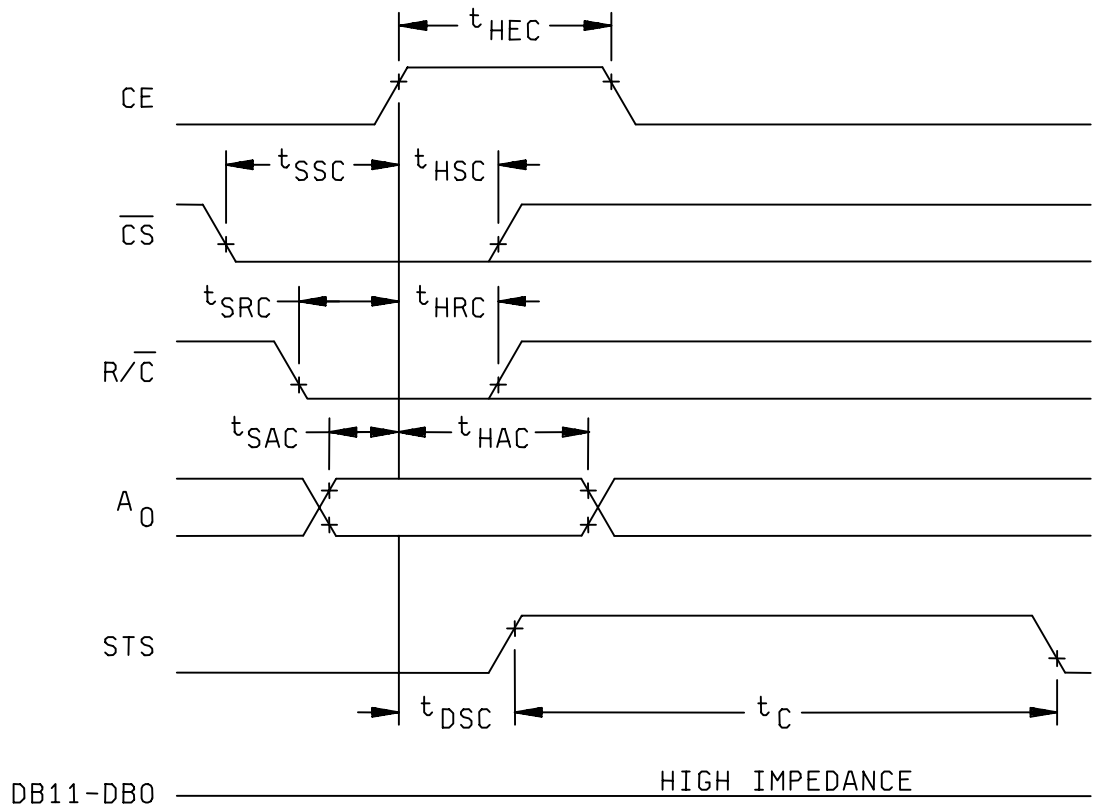


FIGURE 4. Converter start timing diagram.

<b>STANDARD MICROCIRCUIT DRAWING</b> DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 43216-5000	SIZE <b>A</b>		<b>5962-93164</b>
		REVISION LEVEL <b>A</b>	SHEET <b>13</b>

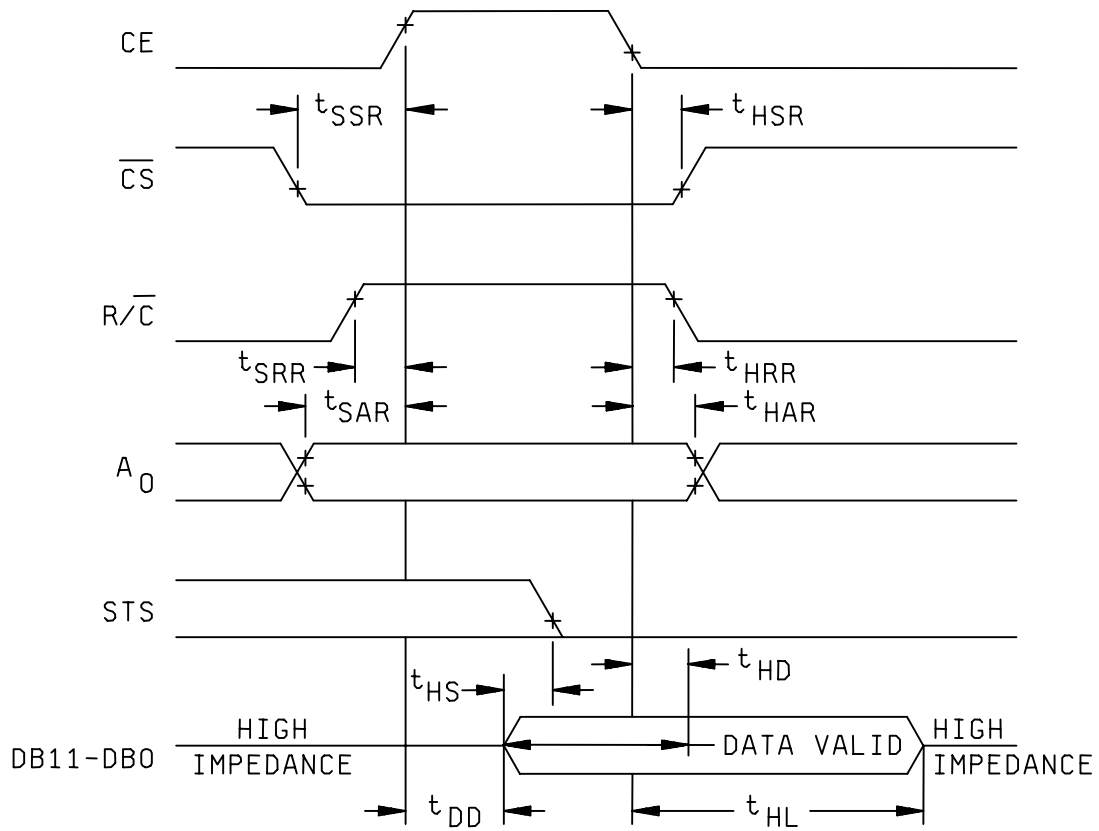


FIGURE 5. Read timing diagram.

**STANDARD  
MICROCIRCUIT DRAWING**  
DEFENSE SUPPLY CENTER COLUMBUS  
COLUMBUS, OHIO 43216-5000

SIZE  
**A**

**5962-93164**

REVISION LEVEL  
**A**

SHEET  
**14**

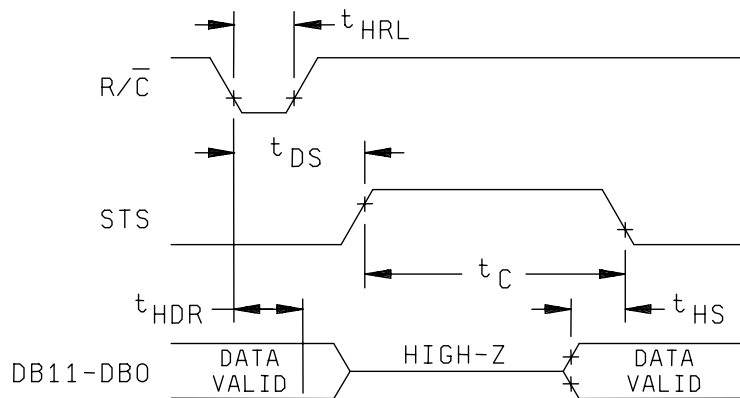


FIGURE 6. Stand-alone mode timing low pulse for  $R/\bar{C}$  diagram.

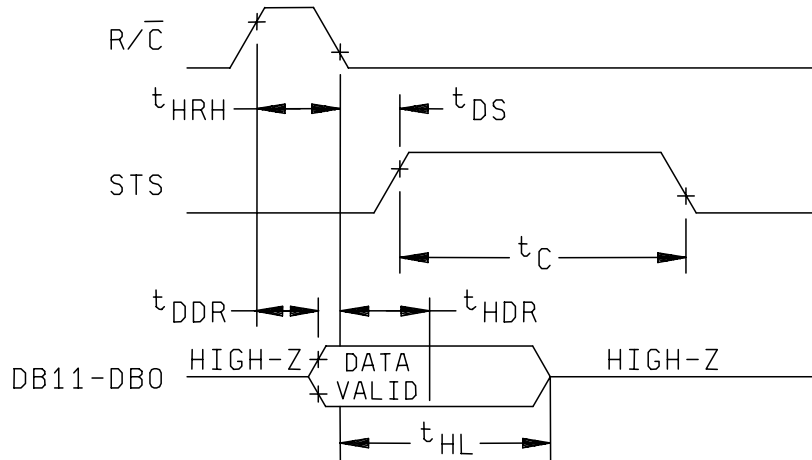


FIGURE 7. Stand-alone mode timing high pulse for  $R/\bar{C}$  diagram.

**STANDARD  
MICROCIRCUIT DRAWING**  
DEFENSE SUPPLY CENTER COLUMBUS  
COLUMBUS, OHIO 43216-5000

SIZE  
**A**

**5962-93164**

REVISION LEVEL  
**A**

SHEET  
**15**

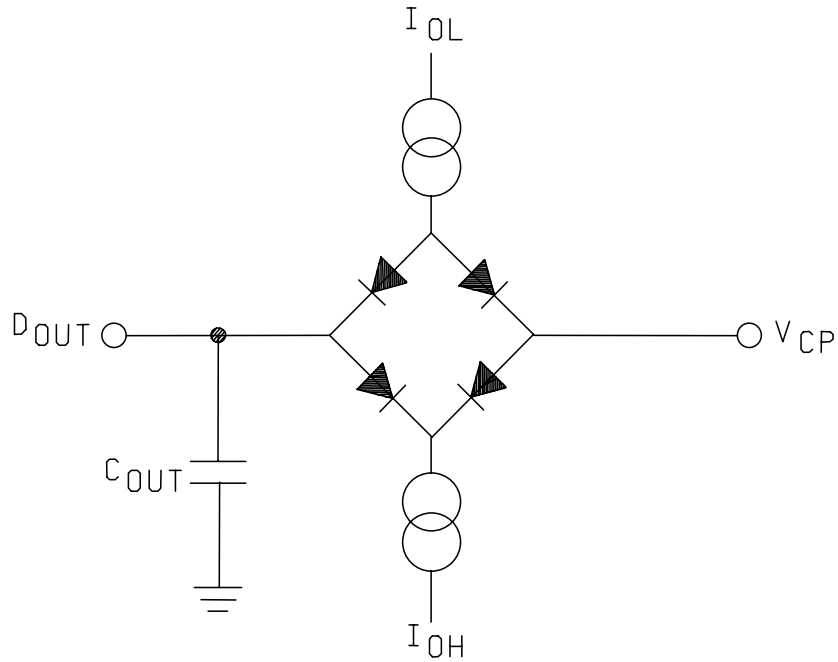


FIGURE 8. Load circuit for bus timing specifications.

Test	V <sub>CP</sub>	C <sub>OUT</sub>
Access time high Z to logic low	5 V	100 pF
Float time logic high to high Z	0 V	10 pF
Access time high Z to logic high	0 V	100 pF
Float time logic low to high Z	5 V	10 pF

FIGURE 9. Load conditions for bus timing specifications.

**STANDARD  
MICROCIRCUIT DRAWING**  
DEFENSE SUPPLY CENTER COLUMBUS  
COLUMBUS, OHIO 43216-5000

SIZE  
**A**

REVISION LEVEL  
**A**

**5962-93164**

SHEET  
**16**



4. QUALITY ASSURANCE PROVISIONS

4.1 Sampling and inspection. For device classes Q and V, sampling and inspection procedures shall be in accordance with MIL-PRF-38535 or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein. For device class M, sampling and inspection procedures shall be in accordance with MIL-PRF-38535, appendix A.

4.2 Screening. For device classes Q and V, screening shall be in accordance with MIL-PRF-38535, and shall be conducted on all devices prior to qualification and technology conformance inspection. For device class M, screening shall be in accordance with method 5004 of MIL-STD-883, and shall be conducted on all devices prior to quality conformance inspection.

4.2.1 Additional criteria for device class M.

- a. Burn-in test, method 1015 of MIL-STD-883.
  - (1) Test condition A, B, C, or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015.
  - (2) T<sub>A</sub> = +125°C, minimum.
- b. Interim and final electrical test parameters shall be as specified in table II herein.

4.2.2 Additional criteria for device classes Q and V.

- a. The burn-in test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The burn-in test circuit shall be maintained under document revision level control of the device manufacturer's Technology Review Board (TRB) in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015 of MIL-STD-883.
- b. Interim and final electrical test parameters shall be as specified in table II herein.
- c. Additional screening for device class V beyond the requirements of device class Q shall be as specified in MIL-PRF-38535, appendix B.

4.3 Qualification inspection for device classes Q and V. Qualification inspection for device classes Q and V shall be in accordance with MIL-PRF-38535. Inspections to be performed shall be those specified in MIL-PRF-38535 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4).

4.4 Conformance inspection. Technology conformance inspection for classes Q and V shall be in accordance with MIL-PRF-38535 including groups A, B, C, D, and E inspections and as specified herein. Quality conformance inspection for device class M shall be in accordance with MIL-PRF-38535, appendix A and as specified herein. Inspections to be performed for device class M shall be those specified in method 5005 of MIL-STD-883 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4).

4.4.1 Group A inspection.

- a. Tests shall be as specified in table II herein.
- b. For device class M, subgroups 7 and 8 tests shall be sufficient to verify the truth table. For device classes Q and V, subgroups 7 and 8 shall include verifying the functionality of the device.

<b>STANDARD MICROCIRCUIT DRAWING</b> DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 43216-5000	SIZE <b>A</b>		<b>5962-93164</b>
		REVISION LEVEL <b>A</b>	SHEET <b>17</b>

TABLE II. Electrical test requirements.

Test requirements	Subgroups (in accordance with MIL-STD-883, method 5005, table I)	Subgroups (in accordance with MIL-PRF-38535, table III)	
	Device class M	Device class Q	Device class V
Interim electrical parameters (see 4.2)	1	1	1
Final electrical parameters (see 4.2)	1,2,3,9 <u>1/</u>	1,2,3,9 <u>1/</u>	1,2,3,9 <u>1/</u>
Group A test requirements (see 4.4)	1,2,3,4,5,6,9,10,11	1,2,3,4,5,6, 9,10,11	1,2,3,4,5,6, 9,10,11
Group C end-point electrical parameters (see 4.4)	1	1	1,2,3
Group D end-point electrical parameters (see 4.4)	1	1	1,2,3
Group E end-point electrical parameters (see 4.4)	---	---	---

1/ PDA applies to subgroup 1.

4.4.2 Group C inspection. The group C inspection end-point electrical parameters shall be as specified in table II herein.

4.4.2.1 Additional criteria for device class M. Steady-state life test conditions, method 1005 of MIL-STD-883:

- a. Test condition A, B, C, or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1005 of MIL-STD-883.
- b.  $T_A = +125^{\circ}\text{C}$ , minimum.
- c. Test duration: 1,000 hours, except as permitted by method 1005 of MIL-STD-883.

4.4.2.2 Additional criteria for device classes Q and V. The steady-state life test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The test circuit shall be maintained under document revision level control by the device manufacturer's TRB in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1005 of MIL-STD-883.

4.4.3 Group D inspection. The group D inspection end-point electrical parameters shall be as specified in table II herein.

<b>STANDARD MICROCIRCUIT DRAWING</b> DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 43216-5000	SIZE <b>A</b>		<b>5962-93164</b>
		REVISION LEVEL <b>A</b>	SHEET <b>18</b>

4.4.4 Group E inspection. Group E inspection is required only for parts intended to be marked as radiation hardness assured (see 3.5 herein).

- a. End-point electrical parameters shall be as specified in table II herein.
- b. For device classes Q and V, the devices or test vehicle shall be subjected to radiation hardness assured tests as specified in MIL-PRF-38535 for the RHA level being tested. For device class M, the devices shall be subjected to radiation hardness assured tests as specified in MIL-PRF-38535, appendix A for the RHA level being tested. All device classes must meet the post irradiation end-point electrical parameter limits as defined in table I at  $T_A = +25^{\circ}\text{C} \pm 5^{\circ}\text{C}$ , after exposure, to the subgroups specified in table II herein.
- c. When specified in the purchase order or contract, a copy of the RHA delta limits shall be supplied.

## 5. PACKAGING

5.1 Packaging requirements. The requirements for packaging shall be in accordance with MIL-PRF-38535 for device classes Q and V or MIL-PRF-38535, appendix A for device class M.

## 6. NOTES

6.1 Intended use. Microcircuits conforming to this drawing are intended for use for Government microcircuit applications (original equipment), design applications, and logistics purposes.

6.1.1 Replaceability. Microcircuits covered by this drawing will replace the same generic device covered by a contractor prepared specification or drawing.

6.1.2 Substitutability. Device class Q devices will replace device class M devices.

6.2 Configuration control of SMD's. All proposed changes to existing SMD's will be coordinated with the users of record for the individual documents. This coordination will be accomplished using DD Form 1692, Engineering Change Proposal.

6.3 Record of users. Military and industrial users should inform Defense Supply Center Columbus when a system application requires configuration control and which SMD's are applicable to that system. DSCC will maintain a record of users and this list will be used for coordination and distribution of changes to the drawings. Users of drawings covering microelectronic devices (FSC 5962) should contact DSCC-VA, telephone (614) 692-0544.

6.4 Comments. Comments on this drawing should be directed to DSCC-VA, Columbus, Ohio 43216-5000, or telephone (614) 692-0547.

6.5 Abbreviations, symbols, and definitions. The abbreviations, symbols, and definitions used herein are defined in MIL-PRF-38535 and MIL-HDBK-1331.

6.6 Sources of supply.

6.6.1 Sources of supply for device classes Q and V. Sources of supply for device classes Q and V are listed in QML-38535. The vendors listed in QML-38535 have submitted a certificate of compliance (see 3.6 herein) to DSCC-VA and have agreed to this drawing.

6.6.2 Approved sources of supply for device class M. Approved sources of supply for class M are listed in MIL-HDBK-103. The vendors listed in MIL-HDBK-103 have agreed to this drawing and a certificate of compliance (see 3.6 herein) has been submitted to and accepted by DSCC-VA.

<b>STANDARD MICROCIRCUIT DRAWING</b> DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 43216-5000	SIZE <b>A</b>		<b>5962-93164</b>
		REVISION LEVEL <b>A</b>	SHEET <b>19</b>

STANDARD MICROCIRCUIT DRAWING BULLETIN

DATE: 02-03-07

Approved sources of supply for SMD 5962-93164 are listed below for immediate acquisition information only and shall be added to MIL-HDBK-103 and QML-38535 during the next revision. MIL-HDBK-103 and QML-38535 will be revised to include the addition or deletion of sources. The vendors listed below have agreed to this drawing and a certificate of compliance has been submitted to and accepted by DSCC-VA. This bulletin is superseded by the next dated revision of MIL-HDBK-103 and QML-38535.

Standard microcircuit drawing PIN <u>1/</u>	Vendor CAGE number	Vendor similar PIN <u>2/</u>
5962-9316401MXA	24355	AD1674TD/883B

- 1/ The lead finish shown for each PIN representing a hermetic package is the most readily available from the manufacturer listed for that part. If the desired lead finish is not listed contact the vendor to determine its availability.
- 2/ Caution. Do not use this number for item acquisition. Items acquired to this number may not satisfy the performance requirements of this drawing.

Vendor CAGE  
number

24355

Vendor name  
and address

Analog Devices  
Route 1 Industrial Park  
P.O. Box 9106  
Norwood, MA 02062  
Point of contact: 804 Woburn Street  
Wilmington, MA 01887-3462

The information contained herein is disseminated for convenience only and the Government assumes no liability whatsoever for any inaccuracies in the information bulletin.



## Стандарт Электрон Связь

Мы молодая и активно развивающаяся компания в области поставок электронных компонентов. Мы поставляем электронные компоненты отечественного и импортного производства напрямую от производителей и с крупнейших складов мира.

Благодаря сотрудничеству с мировыми поставщиками мы осуществляем комплексные и плановые поставки широчайшего спектра электронных компонентов.

Собственная эффективная логистика и склад в обеспечивает надежную поставку продукции в точно указанные сроки по всей России.

Мы осуществляем техническую поддержку нашим клиентам и предпродажную проверку качества продукции. На все поставляемые продукты мы предоставляем гарантию .

Осуществляем поставки продукции под контролем ВП МО РФ на предприятия военно-промышленного комплекса России , а также работаем в рамках 275 ФЗ с открытием отдельных счетов в уполномоченном банке. Система менеджмента качества компании соответствует требованиям ГОСТ ISO 9001.

Минимальные сроки поставки, гибкие цены, неограниченный ассортимент и индивидуальный подход к клиентам являются основой для выстраивания долгосрочного и эффективного сотрудничества с предприятиями радиоэлектронной промышленности, предприятиями ВПК и научно-исследовательскими институтами России.

С нами вы становитесь еще успешнее!

### Наши контакты:

**Телефон:** +7 812 627 14 35

**Электронная почта:** [sales@st-electron.ru](mailto:sales@st-electron.ru)

**Адрес:** 198099, Санкт-Петербург,  
Промышленная ул, дом № 19, литера Н,  
помещение 100-Н Офис 331